8-Bit Serial or Parallel-Input/ Serial-Output Shift Register

High–Performance Silicon–Gate CMOS

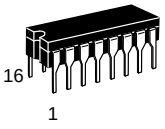
MC54/74HC165

The MC54/74HC165 is identical in pinout to the LS165. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

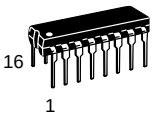
This device is an 8–bit shift register with complementary outputs from the last stage. Data may be loaded into the register either in parallel or in serial form. When the Serial Shift/Parallel Load input is low, the data is loaded asynchronously in parallel. When the Serial Shift/Parallel Load input is high, the data is loaded serially on the rising edge of either Clock or Clock Inhibit (see the Function Table).

The 2–input NOR clock may be used either by combining two independent clock sources or by designating one of the clock inputs to act as a clock inhibit.

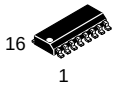
- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 286 FETs or 71.5 Equivalent Gates



J SUFFIX
CERAMIC PACKAGE
CASE 620–10



N SUFFIX
PLASTIC PACKAGE
CASE 648–08

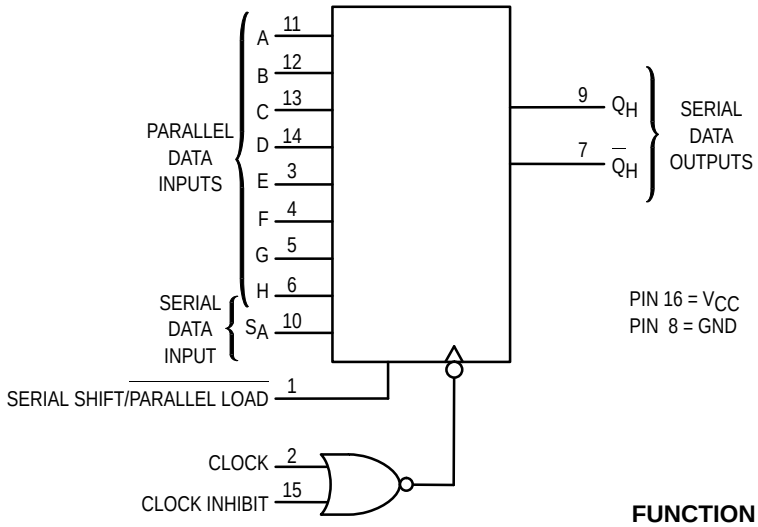


D SUFFIX
SOIC PACKAGE
CASE 751B–05

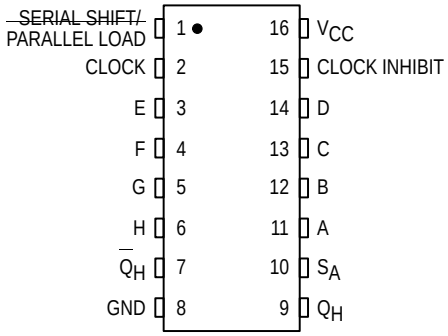
ORDERING INFORMATION

MC54HCXXXJ	Ceramic
MC74HCXXXN	Plastic
MC74HCXXXD	SOIC

LOGIC DIAGRAM



PIN ASSIGNMENT



FUNCTION TABLE

Inputs					Internal Stages		Output	
Serial Shift/ Parallel Load	Clock	Clock Inhibit	S_A	A – H	Q_A	Q_B	Q_H	Operation
L	X	X	X	a … h	a	b	h	Asynchronous Parallel Load
H H	↗ ↗	L L	L H	X X	L H	Q_{An} Q_{An}	Q_{Gn} Q_{Gn}	Serial Shift via Clock
H H	L L	↗ ↗	L H	X X	L H	Q_{An} Q_{An}	Q_{Gn} Q_{Gn}	Serial Shift via Clock Inhibit
H H	X H	H X	X X	X X	No Change			Inhibited Clock
H	L	L	X	X	No Change			No Clock

X = don't care
Q_{An} – Q_{Gn} = Data shifted from the preceding stage

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	– 1.5 to V_{CC} + 1.5	V
V_{out}	DC Output Voltage (Referenced to GND)	– 0.5 to V_{CC} + 0.5	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	 260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

* Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C
Ceramic DIP: – 10 mW/°C from 100° to 125°C
SOIC Package: – 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		– 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	V_{CC} = 2.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				– 55 to 25°C	≤ 85°C	≤ 125°C	
V_{IH}	Minimum High–Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\|I_{out}\|$ ≤ 20 μA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum Low–Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\|I_{out}\|$ ≤ 20 μA	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0 9 1.2	0.3 0.9 1.2	V
V_{OH}	Minimum High–Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 4.0 mA $\|I_{out}\|$ ≤ 5.2 mA	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	V
V_{OL}	Maximum Low–Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 20 μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 4.0 mA $\|I_{out}\|$ ≤ 5.2 mA	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	
I_{in}	Maximum Input Leakage Current	V_{in} = V_{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{in} = V_{CC} or GND I_{out} = 0 μA	6.0	8	80	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			– 55 to 25°C	≤ 85°C	≤ 125°C	
f_{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 8)	2.0 4.5 6.0	6.0 30 35	4.8 24 28	4.0 20 24	MHz
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Clock (or Clock Inhibit) to Q_H or $\overline{Q_H}$ (Figures 1 and 8)	2.0 4.5 6.0	150 30 26	190 38 33	225 45 38	ns
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Serial Shift/Parallel Load to Q_H or $\overline{Q_H}$ (Figures 2 and 8)	2.0 4.5 6.0	175 35 30	220 44 37	265 53 45	ns
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input H to Q_H or $\overline{Q_H}$ (Figures 3 and 8)	2.0 4.5 6.0	150 30 26	190 38 33	225 45 38	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 8)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF

NOTES:
1. For propagation delays with loads other than 50 pF, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).
2. Information on typical parametric values can be found in Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	85	pF

* Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6$ ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			– 55 to 25°C	≤ 85°C	≤ 125°C	
t_{su}	Minimum Setup Time, Parallel Data Inputs to Serial Shift/Parallel Load (Figure 4)	2.0 4.5 6.0	100 20 17	125 25 21	150 30 26	ns
t_{su}	Minimum Setup Time, Input SA to Clock (or Clock Inhibit) (Figure 5)	2.0 4.5 6.0	100 20 17	125 25 21	150 30 26	ns
t_{su}	Minimum Setup Time, Serial Shift/Parallel Load to Clock (or Clock Inhibit) (Figure 6)	2.0 4.5 6.0	100 20 17	125 25 21	150 30 26	ns
t_{su}	Minimum Setup Time, Clock to Clock Inhibit (Figure 7)	2.0 4.5 6.0	100 20 17	125 25 21	150 30 26	ns
t_h	Minimum Hold Time, Serial Shift/Parallel Load to Parallel Data Inputs (Figure 4)	2.0 4.5 6.0	5 5 5	5 5 5	5 5 5	ns
t_h	Minimum Hold Time, Clock (or Clock Inhibit) to Input SA (Figure 5)	2.0 4.5 6.0	5 5 5	5 5 5	5 5 5	ns
t_h	Minimum Hold Time, Clock (or Clock Inhibit) to Serial Shift/Parallel Load (Figure 6)	2.0 4.5 6.0	5 5 5	5 5 5	5 5 5	ns
t_{rec}	Minimum Recovery Time, Clock to Clock Inhibit (Figure 7)	2.0 4.5 6.0	100 20 17	125 25 21	150 30 26	ns
t_w	Minimum Pulse Width, Clock (or Clock Inhibit) (Figure 1)	2.0 4.5 6.0	80 16 14	100 20 17	120 24 20	ns
t_w	Minimum Pulse width, Serial Shift/Parallel Load (Figure 2)	2.0 4.5 6.0	80 16 14	100 20 17	120 24 20	ns
t_r, t_f	Maximum Input Rise and Fall Times (Figure 1)	2.0 4.5 6.0	1000 500 400	1000 500 400	1000 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS

A, B, C, D, E, F, G, H (Pins 11, 12, 13, 14, 3, 4, 5, 6)

Parallel Data inputs. Data on these inputs are asynchronously entered in parallel into the internal flip–flops when the Serial Shift/Parallel Load input is low.

SA (Pin 10)

Serial Data input. When the Serial Shift/Parallel Load input is high, data on this pin is serially entered into the first stage of the shift register with the rising edge of the Clock.

CONTROL INPUTS

Serial Shift/Parallel Load (Pin 1)

Data–entry control input. When a high level is applied to this pin, data at the Serial Data input (SA) are shifted into the register with the rising edge of the Clock. When a low level is applied to this pin, data at the Parallel Data inputs are asynchronously loaded into each of the eight internal stages.

Clock, Clock Inhibit (Pins 2, 15)

Clock inputs. These two clock inputs function identically. Either may be used as an active–high clock inhibit. However, to avoid double clocking, the inhibit input should go high only while the clock input is high.

The shift register is completely static, allowing Clock rates down to DC in a continuous or intermittent mode.

OUTPUTS

Q_H, $\overline{Q}_H$ (Pins 9, 7)

Complementary Shift Register outputs. These pins are the noninverted and inverted outputs of the eighth stage of the shift register.

SWITCHING WAVEFORMS

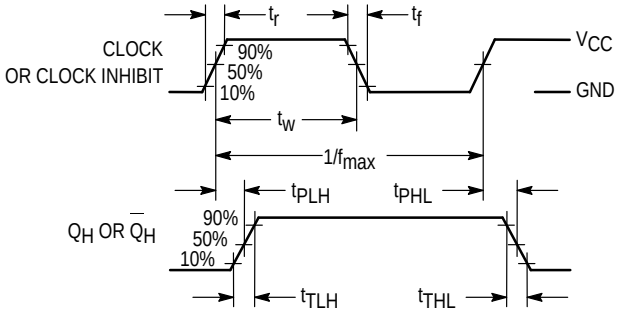


Figure 1. Serial–Shift Mode

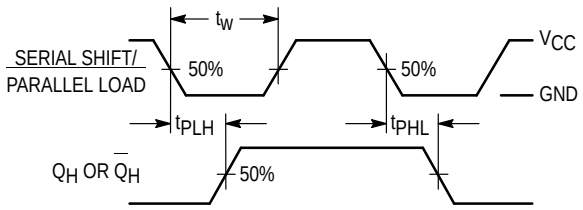


Figure 2. Parallel–Load Mode

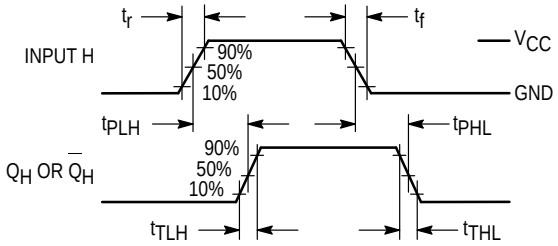


Figure 3. Parallel–Load Mode

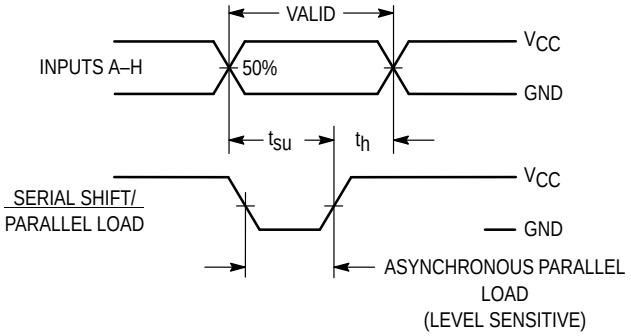


Figure 4. Parallel–Load Mode

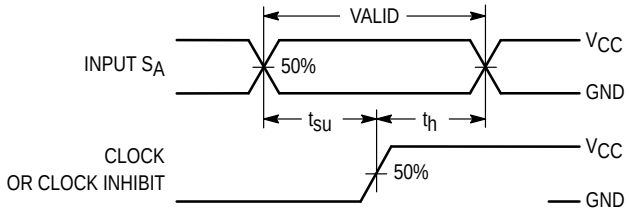


Figure 5. Serial–Shift Mode

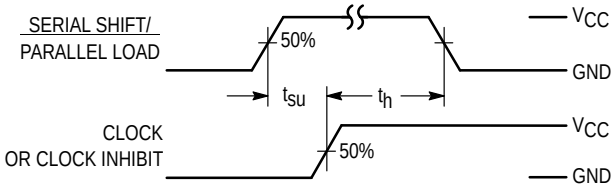


Figure 6. Serial–Shift Mode

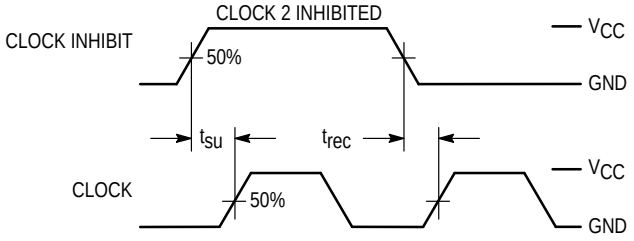
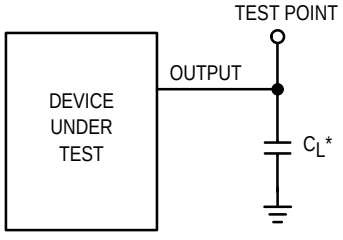


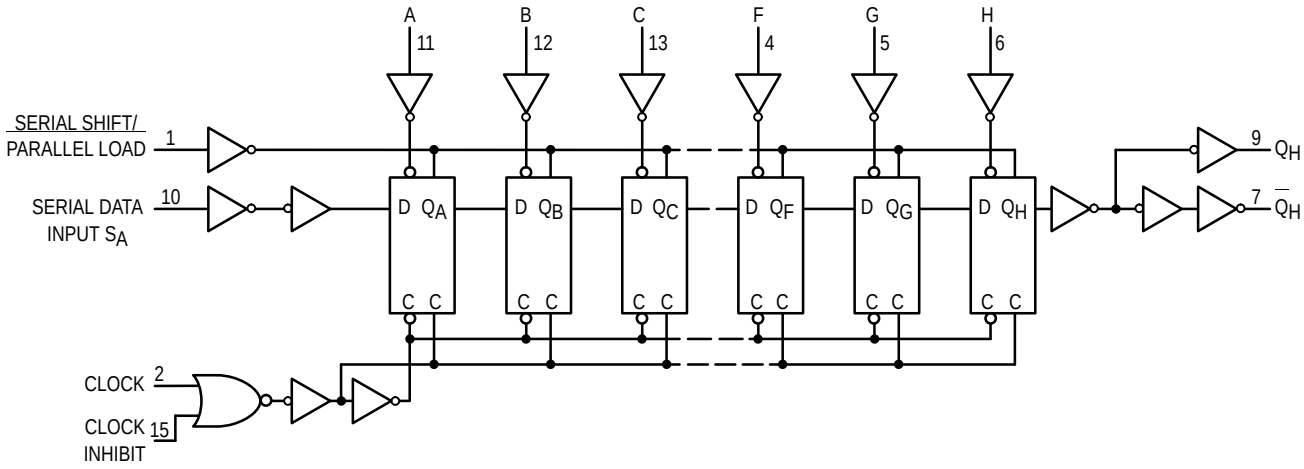
Figure 7. Serial–Shift, Clock–Inhibit Mode



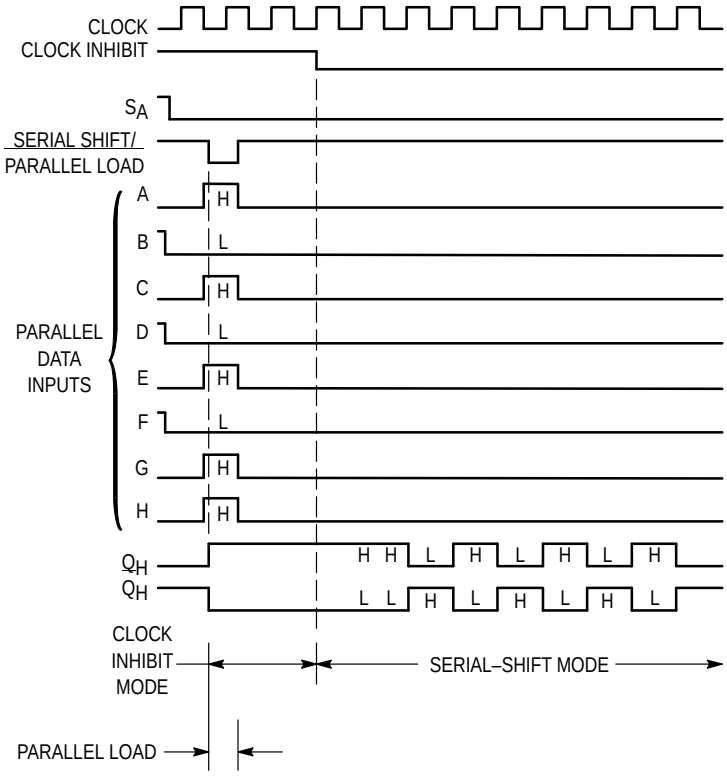
* Includes all probe and jig capacitance

Figure 8. Test Circuit

EXPANDED LOGIC DIAGRAM

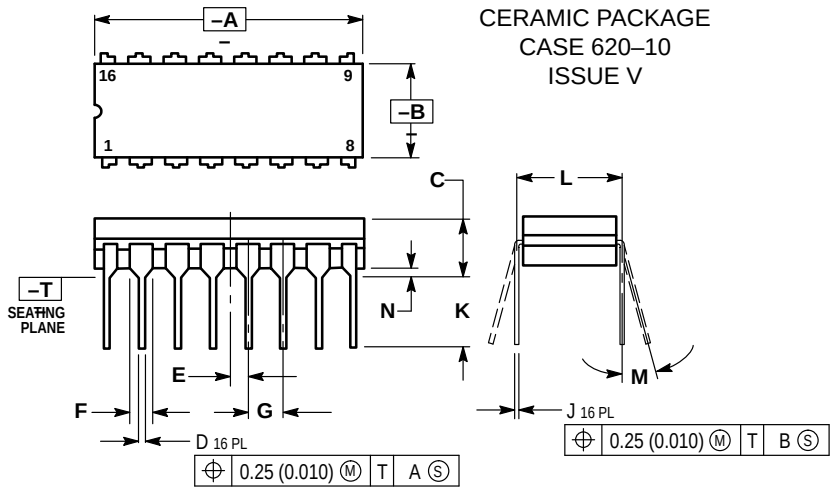


TIMING DIAGRAM



OUTLINE DIMENSIONS

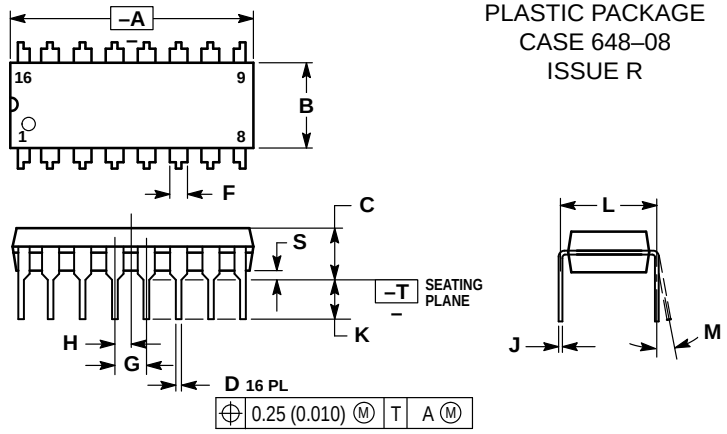
J SUFFIX
CERAMIC PACKAGE
CASE 620–10
ISSUE V



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIM F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	—	0.200	—	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

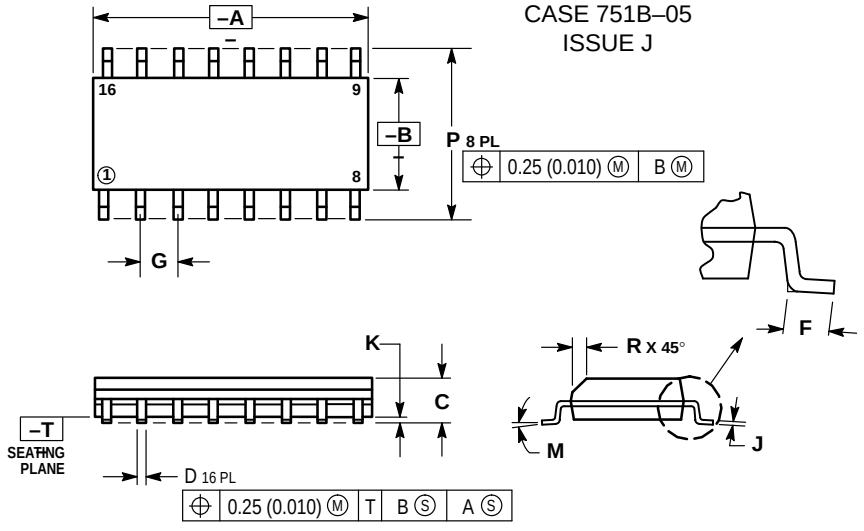
N SUFFIX
PLASTIC PACKAGE
CASE 648–08
ISSUE R



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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